

## **INCHANGE SEMICONDUCTOR**

## isc N-Channel MOSFET Transistor TK10E80

## **TK10E80W, ITK10E80W**

## • FEATURES

- Low drain-source on-resistance: R⊳s(on) ≤0.55Ω.
- Enhancement mode:

Vth =3.0 to 4.0V (VDs = 10 V, ID=0.45mA)

- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

Switching Voltage Regulators

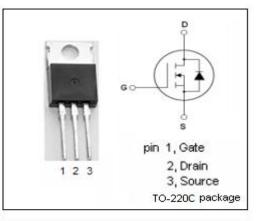
#### • ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

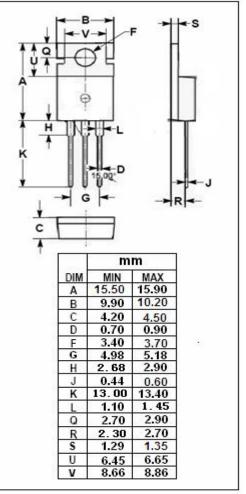
SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>DSS</sub>	Drain-Source Voltage	800	V				
V <sub>GS</sub>	Gate-Source Voltage	±20	V				
ID	Drain Current-Continuous	9.5	A				
I <sub>DM</sub>	Drain Current-Single Pulsed	38	A				
PD	Total Dissipation @Tc=25°C	130	W				
Tj	Max. Operating Junction Temperature	150	°C				
T <sub>stg</sub>	Storage Temperature	-55~150	°C				

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT		
Rth(ch-c)	Channel-to-case thermal resistance	0.962	°C/W		
Rth(ch-a) Channel-to-ambient thermal resistance		83.3	°C/W		

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#### isc website: www.iscsemi.cn



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#### **ELECTRICAL CHARACTERISTICS**

 $T_c=25^{\circ}C$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =10mA	800			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =10V; I <sub>D</sub> =0.45mA	3.0		4.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =4.8A			0.55	Ω
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V			±1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =800V; V <sub>GS</sub> = 0V			10	μA
VSDF	Diode forward voltage	I <sub>DR</sub> =9.5A, V <sub>GS</sub> = 0 V			1.7	V

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